L Number	Hits	Search Text	DB	Time stamp
1	7	gate adj (oxide insulator) WITH diode near3 reverse adj breakdown	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/19 11:33
2	3774	((257/173,355-358,360-363) or (361/56,111)).CCLS.	USPAT; US-PGPUB	2003/06/19 12:08
3	200	(((257/173,355-358,360-363) or (361/56,111)).CCLS.) and @pd > "20030113"	USPAT; US-PGPUB	2003/06/19 12:09
4	71	((((257/173,355-358,360-363) or (361/56,111)).CCLS.) and @pd > "20030113") and (esd electrostatic adj discharge)	USPAT	2003/06/19 12:10
5	2326	reverse adj breakdown	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/19 12:14
6	1168	breakdown near3 gate adj (oxide insulator)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/19 12:14
8	1257	(reverse adj breakdown) and input	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/19 12:15
9	45	core adj region and I/O adj region	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/19 12:15
11	1313	protection with diode and cmos	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/19 12:15
12	3523	input adj pad	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/19 12:15
7	227	((reverse adj breakdown) and input) and (protection with diode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/19 12:16
10	1	(protection with diode and cmos) and core adj region	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/19 12:16
13	40	(reverse adj breakdown) and (breakdown near3 gate adj (oxide insulator))	USPAT; US-PGPUB	2003/06/19 12:16
14	71	(((((257/173,355-358,360-363) or (361/56,111)).CCLS.) and @pd > "20030113") and (esd electrostatic adj discharge))	USPAT; US-PGPUB	2003/06/19 12:16
15	332	((((reverse adj breakdown) and input) and (protection with diode)) ((reverse adj breakdown) and input) (core adj region and I/O adj region) ((protection with diode and cmos) and core adj region) (protection with diode and cmos) (input adj pad) ((reverse adj breakdown) and (breakdown near3 gate adj (oxide insulator))) (((((257/173,355-358,360-363) or (361/56,111)).CCLS.) and @pd > "20030113") and (esd electrostatic adj discharge))) and @pd > "20030113"	USPAT; US-PGPUB	2003/06/19 12:17

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| 16 | 139 | (((((reverse adj breakdown) and input) and (protection with diode)) ((reverse adj breakdown) and input) (core adj region and I/O adj region) ((protection with diode and cmos) and core adj region) (protection with diode and cmos) (input adj pad) ((reverse adj breakdown) and (breakdown near3 gate adj (oxide insulator))) (((((257/173,355-358,360-363) or (361/56,111)).CCLS.) and @pd > "20030113") and (esd electrostatic adj discharge))) and @pd > "20030113") not (input adj pad) | USPAT; US-PGPUB | 2003/06/19 12.17 |
| 17 | 267 | ((((257/173,355-358,360-363) or (361/56,111)).CCLS.) and @pd > "20030113") ((((((reverse adj breakdown) and input) and (protection with diode)) ((reverse adj breakdown) and input) (core adj region and I/O adj region) ((protection with diode and cmos) and core adj region) (protection with diode and cmos) (input adj pad) ((reverse adj breakdown) and (breakdown near3 gate adj (oxide insulator))) (((((257/173,355-358,360-363) or (361/56,111)).CCLS.) and @pd > "20030113") and (esd electrostatic adj discharge))) and @pd > "20030113") not (input adj pad)) | USPAT; US-PGPUB | 2003/06/19 12.17 |

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